

Low sintering temperature of ZnNb_2O_6 for silver co-sintering

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Abstract

The purpose of this study is the making of multilayer type I capacitors composed of ZnNb_2O_6 co-sintered with silver electrodes. In order to lower the sintering temperature, we have mixed three commercially available glass frit powders with ZnNb_2O_6 . The sintering behaviours were studied by thermomechanical analysis (TMA). Two additives allowed us to sinter ZnNb_2O_6 at 900 °C. The sintered ceramic pellets show a type I dielectric behaviour close to the one of pure ZnNb_2O_6 (e.g.: dielectric constant around 22, resistivity above $10^{12} \Omega$ and dielectric losses lower than 10^{-3}). Ceramics were co-sintered with Ag in order to estimate Ag diffusion behaviour. One composition, $\text{ZnNb}_2\text{O}_6+5 \text{ wt\% (B}_2\text{O}_3\text{–ZnO–SiO}_2\text{)}$ glass frit can be co-sintered at 900 °C with Ag electrodes and leads to type I dielectric properties.

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1. Introduction

First investigated by Maeda et al. [1], ZnNb_2O_6 has the best dielectric properties (dielectric constant equals to 25 and high quality factor of 8370) among the isostructural orthorhombic columbite structure MNb_2O_6 (where $\text{M}=\text{Ca}^{2+}$, Co^{2+} , Mn^{2+} , Ni^{2+} and Zn^{2+}) [2]. It may be very promising for microwave applications due to its very high quality factor. When applied to multilayer ceramic capacitors, on account of its high sintering temperature (around 1200 °C), inner electrodes must be Pd or at least a Pd/Ag alloy. Many efforts are devoted to eliminating Pd due to its high cost. Moreover Ag electrodes will own a better electrical conductivity which could improve capacitor electrical performances, notably ESR (Equivalent Series Resistance). It is thus necessary to sinter ZnNb_2O_6 at a temperature lower than 900 °C. Some additives were used in previous studies in order to lower the sintering temperature:

- CuO (5 wt% addition, sintering temperature 925 °C, $\epsilon_r=22$, $QF=59,500 \text{ GHz}$, $\tau_f=-66 \text{ ppm } ^\circ\text{C}^{-1}$) [3];
- $\text{V}_2\text{O}_5\text{–Bi}_2\text{O}_3$ (1 wt% $\text{V}_2\text{O}_5+1 \text{ wt\% Bi}_2\text{O}_3$ addition, sintering temperature 1000 °C, $\epsilon_r=22.9$, $\tan(\delta)<10^{-3}$) [4];
- $\text{V}_2\text{O}_5\text{–Bi}_2\text{O}_3\text{–CuO}$ (1 wt% $\text{V}_2\text{O}_5+1 \text{ wt\% Bi}_2\text{O}_3+2.5 \text{ wt\% CuO}$ addition, sintering temperature 880 °C, $\epsilon_r=23.4$,

$QF=46,975 \text{ GHz}$, $\tau_f=-44.89 \text{ ppm } ^\circ\text{C}^{-1}$) [4] or (1.5 wt% add-on, sintering temperature 890 °C, $\epsilon_r=32.69$, $QF=67,100 \text{ GHz}$, $\tau_f=-32.69 \text{ ppm } ^\circ\text{C}^{-1}$) [5] or the same material but cosintered with pure Ag [6];

- $\text{B}_2\text{O}_3\text{–CuO}$ (5 wt% CuO+2 wt% B_2O_3 addition, sintering temperature 900 °C, $\epsilon_r=22.5$, $QF=55,000 \text{ GHz}$, $\tau_f=-25 \text{ ppm } ^\circ\text{C}^{-1}$) [7]; and
- $\text{B}_2\text{O}_3\text{–ZnO–SiO}_2$ (5 wt% addition, sintering temperature 925/975 °C, $\epsilon_r=22.5/21.3$, $QF=12,800/38,000 \text{ GHz}$, $\tau_f=-69.6/-66.0 \text{ ppm } ^\circ\text{C}^{-1}$) [8].

Yet, in these literatures, Ag co-sintering was not performed [4,5,7,8], or microstructural and dielectric properties were not published [3,6].

We shall present here the sintering behaviour, the structural and microstructural analyses together with the electric and dielectric properties of ceramics and Ag co-sintered ceramics, composed of ZnNb_2O_6 mixed with commercial glass frits additives belonging to the composition diagrams $\text{B}_2\text{O}_3\text{–ZnO–SiO}_2$, $\text{B}_2\text{O}_3\text{–ZnO–Bi}_2\text{O}_3$ and $\text{B}_2\text{O}_3\text{–SiO}_2\text{–BaO}$ and owning low softening points (T_g).

2. Experimental procedure

Stoichiometric ZnNb_2O_6 was synthesised by the conventional solid state route from high purity oxide ZnO (>99.8%) and Nb_2O_5 (99.5%). The starting materials were mixed and

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Table 1
Glass frit properties.

Ref.	Datasheet composition (wt%)	EDS (at%)	Calculated composition (wt%)	Density	S_{BET} (m ² /g)/ ϕ_{BET} (μm)	T_g (°C)	ϵ_r	Tan(δ) (%)	ρ (Ω cm)
BZBi	B ₂ O ₃ : 19.0	Bi: 20	B ₂ O ₃ : 19.0	3.6	1.43/1.9	540	11.5	0.2	> 10 ¹²
	Bi ₂ O ₃ : 30–50	Zn: 60	Bi ₂ O ₃ : 51						
	ZnO: 15–35	Si: 10	ZnO: 27						
	SiO ₂ : 1–10	Al: 9	SiO ₂ : 3						
	Al ₂ O ₃ : 1–10		Al ₂ O ₃ : 5						
BZS	B ₂ O ₃ : 24.0	Zn: 79	B ₂ O ₃ : 24.0	5.1	0.16/6.0	640	10.2	10.0	> 10 ¹²
	ZnO: 50–70	Si: 21	ZnO: 64						
	SiO ₂ : 2–15		SiO ₂ : 12						
BSBa	B ₂ O ₃ : 22.5	Ba: 40	B ₂ O ₃ : 22.5	3.7	4.10/0.4	673	1.0	7.0	> 10 ¹²
	BaO: 30–50	Si: 45	BaO: 46						
	SiO ₂ : 15–35	Al: 15	SiO ₂ : 20						
	Al ₂ O ₃ : 2–15		Al ₂ O ₃ : 11						

ground in a high energy laboratory mill (Dyno-Mill Research Lab) with 0.8 mm diameter yttried zirconia balls during a normalised grinding time¹ of 6 min in 50 wt% charged aqueous solution. The powder was dried and calcined in air at 800 °C for 2 h to obtain the pure columbite ZnNb₂O₆ phase (JCPDF File no. 13-0473), identified by X-ray diffraction analysis using Cu-K α radiation with an Inel Equinox 3000 curved detector diffractometer.

The powders were analysed by EDS (ThermoNoran) with a 3400 N Hitachi SEM, and BET specific surface measurements were made with a Micromeritics TriStarII. Glass frits were added to ZnNb₂O₆ with 5% in weight amounts and mixed by milling with a planetary mill (Pulverisette Fritsch P4) in an yttried zirconia bowl with 10 mm diameter balls (same material) for 20 min in ethanol. The densification behaviours of the mixed powders during the sintering cycle were recorded by dilatometric measurements performed in air with a TMA92 Setaram dilatometer with heating rate of 300 °C h⁻¹. Pellets with 10 mm diameter and around 1.5 mm thickness were formed by uniaxial pressing at 2000 kg cm⁻². The sintering was done in free atmosphere at 900 °C with heating and cooling rates of 150 °C h⁻¹, and different dwell times. During sintering, the pellets were placed on a bed of powder with the same composition. After sintering, samples were analysed by XRD and their density was measured with Micromeritics AccuPyc 1330 He pycnometer. Open porosity was estimated by calculating the ratio between He density and geometrical density. Disks were metalised on both faces with pure Ag ink and fired at 780 °C for 20 min in order to achieve a mechanical grip of the electrodes with the ceramic.

1 kHz and 1 V oscillation tension dielectric characterisations (C and $\tan \delta$) were performed with a RCL metre Fluke PM 6306 at 25 °C and moisture regulated to 10% (Secasi SLH100 hot/cold oven with regulated moisture rate). Temperature coefficients of dielectric constant (1 kHz, $V_{\text{osc}}=1$ V) were measured between -30 °C and +145 °C in Secasi SLH100.

¹Defined by whole grinding time \times grinding chamber's volume/whole volume of the slurry. It represents the effective grinding time for each individual powder grain in the slurry.

Insulation resistances were measured in a dry atmosphere (10% moisture) at 25 °C under a 1 V/μm DC bias (Sefelec M1500P megohmmeter). The microwave properties were measured at ambient conditions (Agilent 8720ES Network Analyser).

3. Results and discussion

3.1. Glass frit analyses

The commercial glass frit references will not be given. Instead, the following designations characterising glass frits compositions will be used: B for boron, Z for zinc, S for silicon, Bi for bismuth and Ba for barium.

Table 1 shows for each glass frit designation the compositions given by the producer's datasheet together with the EDS quantitative measurements (boron cannot be quantified with EDS) and the calculated composition, the density and the specific surface together with the calculated BET diameters (with the hypothesis of spherical particles). The deviation in diameter values is very important from a glass frit to another, some powders have very large grains in comparison with the initial ZnNb₂O₆ powder (density = 5.8, $S_{\text{BET}}=10.34$ m²/g, and $\phi_{\text{BET}}=0.1$ μm). Although the granulometry between glass frits and the initial material are different, we achieve a homogeneous powder after grinding. Dielectric and resistivity measurements were performed on pure glass frits sintered 40 °C below T_g with 0.5 h dwell time.

3.2. Dilatometric study

The dilatometric measurements during sintering of pure ZnNb₂O₆ and compositions with different glass frit additions are gathered, Fig. 1. It appears that glass frits BZS and BZBi which contain both Boron and Zinc have a greater effect on the lowering of the sintering temperature compared to the BSBa glass frit. With BZS and BZBi glass frits we could expect to lower the sintering temperature below 900 °C, in order to be compatible with Ag electrodes co-sintering. BSBa addition has a limited effect, allowing only an optimal sintering temperature

close to 1050 °C. It appears that the low softening point is not correlated with the beginning of shrinkage. For BZBi and BZS softening points are respectively 540 °C and 640 °C, but the shrinkage only starts after 700 °C. The same phenomenon is observed for the last glass frit (BSBa): the softening point is 673 °C while the shrinkage occurs only at temperatures higher than 740 °C. So, the low softening point does not seem to be

really influent but the presence of the two chemicals elements boron and zinc in the glass frit should be.

3.3. Samples characterisations

The XRD measurements (Fig. 2) performed on the surface of the pellets indicate the presence of a secondary phase for samples with BZS and BZBi glass frit addition and none with BSBa. One can notice that, whatever the composition of the glass frit is, ZnNb_2O_6 cell parameters are not modified even if substitutions may occur.

For the BZS addition, the secondary phase is Zn_2SiO_4 ($\epsilon_r=6.6$ [9]) which may contribute to a slight lowering of ϵ_r . It is noteworthy that this secondary phase was not detected by Sanoj et al. [8] on a quite similar material ($\text{ZnNb}_2\text{O}_6+5 \text{ wt}\%$ {60 wt% ZnO –30 wt% B_2O_3 –10 wt% SiO_2 glass frit}).

For BZBi, the glass frit induced the formation of BiNbO_4 ($\epsilon_r\approx 43$ [10]). This high dielectric constant will let us expect an increase in the dielectric constant of the pellet. Yet, the amount of secondary phase seems to be very low.

Microstructure observations and EDX analysis confirm the presence of the secondary phases detected with XRD measurements, but also reveal other secondary phases with BZBi and BSBa additions.

Samples with BZS show a darker secondary phase with BSE imaging (Fig. 3A), which was identified as Zn_2SiO_4 phase from semi-quantitative data obtained by EDX (presence of zinc and silicon with an atomic ratio Zn:Si close to 2:1). Calculated porosity from pictures is lower than 2% and is coherent with the porosity measured with He pycnometry.

Fig. 3B is a micrograph of a pellet sintered with BZBi glass frit. EDX analysis on bright areas suggests the presence of BiNbO_4 secondary phase together with $\text{Zn}_3\text{Nb}_2\text{O}_8$ ($\epsilon_r=21.6$ [11]) for the small dark ones. This secondary phase was not detected by XRD analysis, since it was in too small amount to be detected. The image analysis (with ImageJ software) gives a

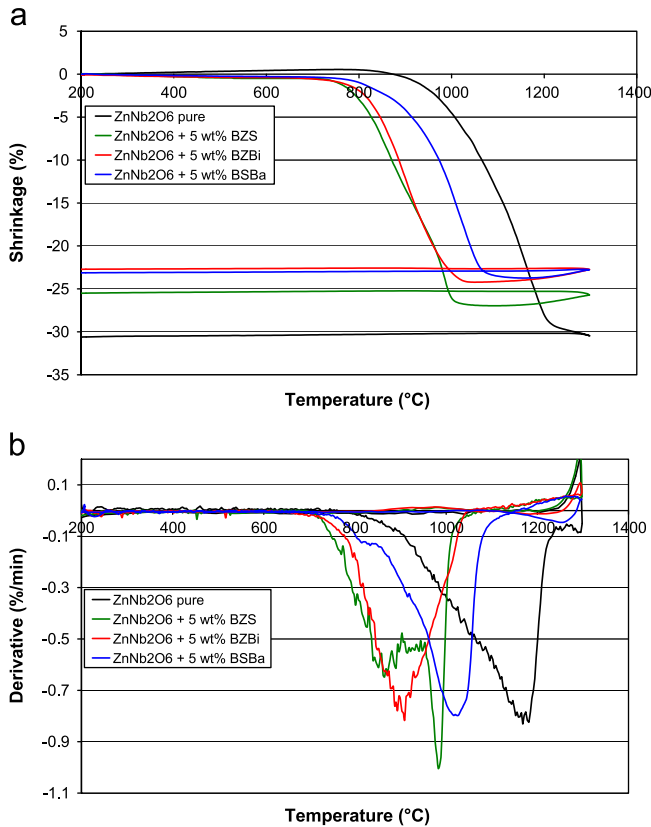


Fig. 1. Dilatometric behaviour of ZnNb_2O_6 with additives: (a) shrinkage behaviour and (b) shrinkage speed.

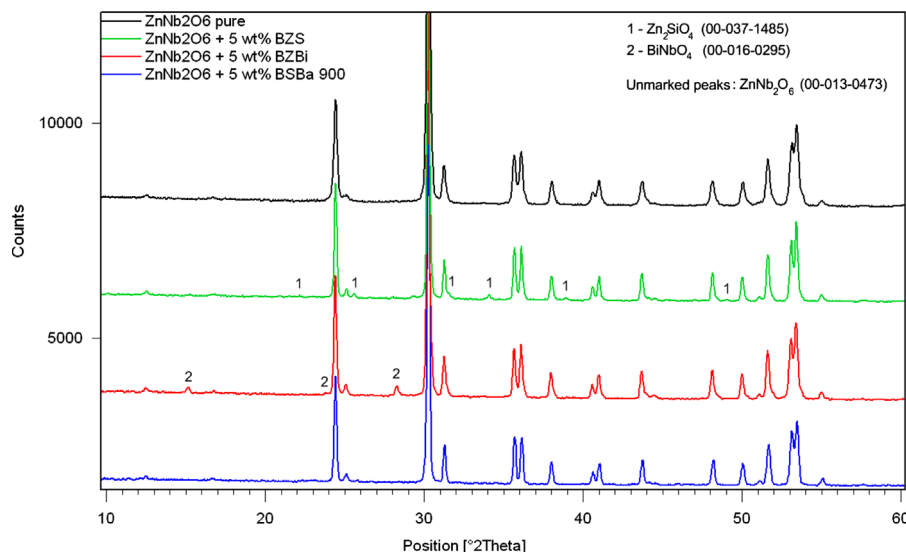


Fig. 2. Diffractograms of ZnNb_2O_6 sintered at 900 °C for 4 h with 5 wt% BZS and BZBi glass frit additions, for 8 h with 5 wt% BSBa glass frit addition.

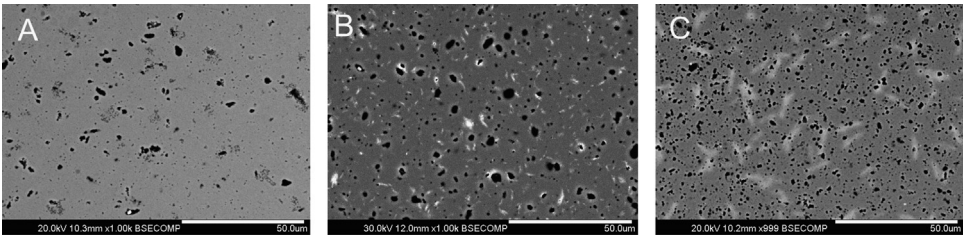


Fig. 3. Microstructure of (A) ZnNb_2O_6 +5 wt% BZS, (B) ZnNb_2O_6 +5 wt% BZBi, and (C) ZnNb_2O_6 +5 wt% BSBa sintered at 900 °C for 4 h (A and B) or 8 h (C).

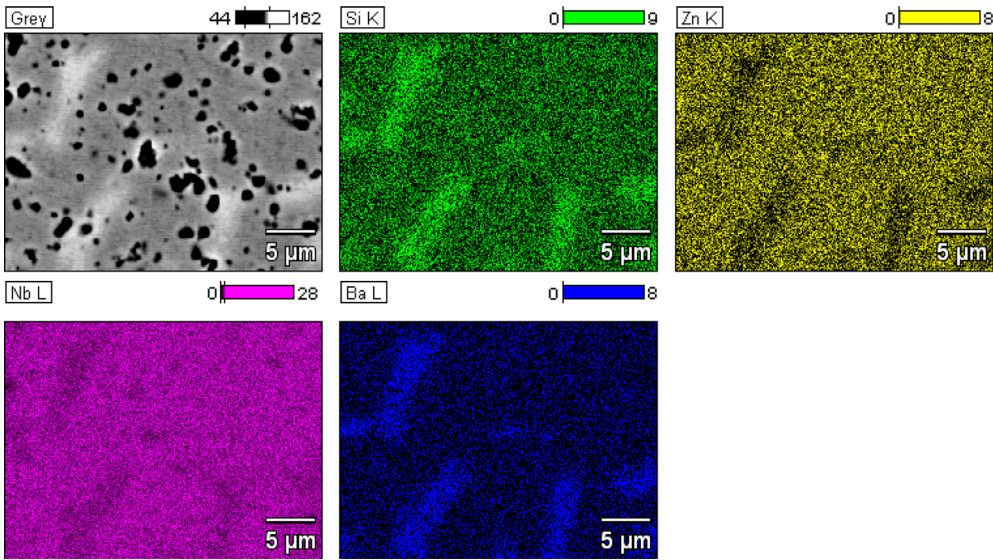


Fig. 4. Spectral imaging of ZnNb_2O_6 +5 wt% BSBa sintered at 900 °C for 8 h.

Table 2
Pellet properties.

Sample ref.	Sintering temperature and dwell time	Shrinkage (%)	Open porosity (%)	ϵ_r	Tan(δ) (%)	ρ (Ω cm)	τ_e (ppm °C ⁻¹)	QF (GHz) at 7.5 GHz
ZnNb_2O_6 pure	1150 °C – 2 h	17.5	≈2	24.0	< 0.1	> 10 ¹²	+147	92,600
ZnNb_2O_6 +5 wt% BZS	900 °C – 4 h	15.9	≈2	21.1	< 0.1	> 10 ¹²	+147	23,070
ZnNb_2O_6 +5 wt% BZBi	900 °C – 4 h	17.0	≈2	22.9	< 0.1	> 10 ¹²	+146	18,230
ZnNb_2O_6 +5 wt% BSBa	900 °C – 8 h	14.1	≈2	21.8	< 0.1	≈10 ¹²	+135	12,640

porosity close to 5%, which is higher than He pycnometry porosity, this should be a closed porosity.

ZnNb_2O_6 with 5 wt% BSBa addition pellets (Fig. 3C) are characterised by elongated bright areas. As shown on spectral imaging (Fig. 4), bright diffuse areas have a composition rich in silicon and barium elements which is similar to the one of the BSBa glass frit (except for boron which could not be quantified with EDX measurement). It should be an amorphous phase as it has not been detected by XRD. The porosity is higher than 10%. As already supposed for BZBi samples, it should be a closed one.

Table 2 gives for each sample: its sintering temperature, dwell time, shrinkage rate, open porosity estimated from the He pycnometric volume, dielectric (ϵ_r , tan(δ), and τ_e) and

electrical (ρ) measurements. The sintering temperature was chosen in order to be compatible with silver cosintering. For ZnNb_2O_6 +5 wt% BSBa which normally has to be sintered at higher temperature (1050 °C), a longer dwell time (8 h) allows a good densification but always slightly lower than the one observed with BZS and BZBi additions.

Among the elements present in the three glass frits, substitutions on A sites seem to be very difficult considering ionic radii with a coordination number of 6 (Nb^{5+} =0.64 Å, Zn^{2+} =0.74 Å, B^{3+} =0.27 Å, Si^{4+} =0.4 Å, Bi^{3+} =1.03 Å, Ba^{2+} =1.35 Å and Al^{3+} =0.535 Å). But, Zn and Al can be considered to substitute Nb on B site of ZnNb_2O_6 . For all the three materials (i.e. ZnNb_2O_6 +5 wt% BZS, ZnNb_2O_6 +5 wt% BZBi and ZnNb_2O_6 +5 wt% BSBa), Zn:Nb ratio in primary phase is

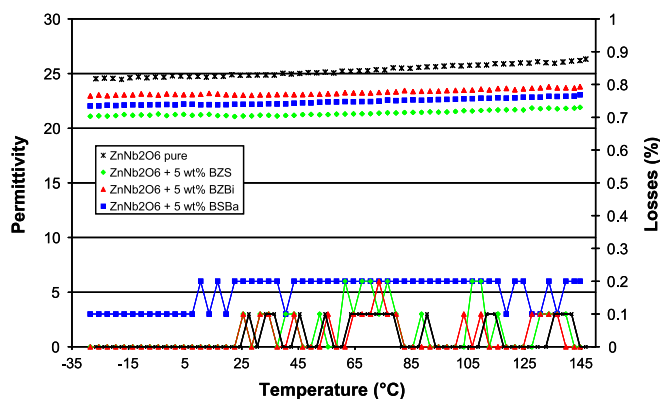


Fig. 5. Dielectric properties vs. temperature of ceramics without Ag co-sintering.

still close to 1:2. So if these substitutions occur they should be limited because they are not detected by XRD and EDX measurements. Even if limited, they should contribute to lowering the sintering temperature due to the appearance of oxygen vacancies on anionic lattice. On the other hand, boron can also contribute to this lowering [12].

These samples are all nearly full densified with only a very low estimated open porosity (lower than 2%). Electrical and dielectric properties of pure ZnNb_2O_6 correspond to those found in the literature e.g.: $\epsilon_r=24$, $\tan(\delta) < 0.1$, $\rho > 10^{12} \Omega \text{ cm}$ [2,13].

As expected, correlated with the presence of the low permittivity Zn_2SiO_4 ($\epsilon_r=6.6$) secondary phase, samples with BZS belong to a ϵ_r lower than the one of pure ZnNb_2O_6 . Contrariwise, BZBi glass frit additions do not lead to a higher ϵ_r in spite of the presence of a secondary phase with $\epsilon_r=43$. Maybe its effects are minored by the presence of $\text{Zn}_3\text{Nb}_2\text{O}_8$ and the 5% porosity. Dielectric losses remain very low ($< 0.1\%$) for all samples, and resistivity is above $10^{12} \Omega \text{ cm}$. Secondary phases are not detrimental to ZnNb_2O_6 properties but affect the microwave properties. For BSBa glass frit addition, we observe a decrease of the resistivity. For the three additions, dielectric constants and losses are stable in temperature (Fig. 5). The electrical and dielectric properties of all these compositions are compatible with type I dielectric applications. All of them have a positive Temperature Coefficient of Permittivity close to $140 \text{ ppm } ^\circ\text{C}^{-1}$.

3.4. Ag electrode co-sintering

All the glass frits used in this work can allow ZnNb_2O_6 to be sintered at a temperature compatible with Ag electrode. Whatever the composition is, linescans EDX analysis made at the Ag/ceramic interface (Fig. 6) do not reveal any Ag diffusion in ZnNb_2O_6 as the composition profile is sharp (if taking in consideration the size of the electron beam).

Compositions with BZS glass frit have the same secondary phase when sintered alone or co-sintered with Ag, when analysed with XRD and SEM (Fig. 7). Moreover, their electrical and dielectrical properties remain very close in both cases.

When co-sintered with an Ag layer, the composition with BZBi additive contents a secondary phase different to the one

identified when sintered alone as illustrated in Fig. 8. The secondary phase of co-sintered samples owns a pyrochlore crystalline structure close to the one of $(\text{Bi}_{0.75}\text{Zn}_{0.25})_2(\text{Nb}_{0.75}\text{Zn}_{0.25})_2\text{O}_7$ (JPDF File no. 54-0971).

SEM observations do not reveal pure Ag in the thickness of the samples but show the presence of very bright areas located around the pores (Fig. 9). The EDX analysis of these areas reveals the presence of Ag, Zn, Nb and Bi. The element ratio is as follows: Zn: 14 at%, Nb: 48 at%, Ag: 16 at% and Bi: 22 at%. On the left of Fig. 9 (up side is Ag electrode), it can be seen that the areas' size of this phase is not homogeneous along the pellet's thickness ($\approx 1.1 \text{ mm}$) but the Ag concentration in these bright areas is nearly constant in the entire sample. It seems that Ag diffusion took place through a porous medium and that it concentrates in this new secondary phase. As this phase migrates easily in the material, we can consider that it may be involved in the sintering mechanisms. When located in A site of the pyrochlore cell with a coordination number of 8, Ag^+ has a radius of 1.28 \AA so it can only substitute Bi^{3+} cation whose radius is 1.17 \AA , but not Zn^{2+} which is 0.9 \AA . Ag^+ with a coordination number of 6 has a radius of 1.15 \AA ; so it cannot substitute neither Nb nor Zn on the B site as Nb^{5+} and Zn^{2+} have a ionic radius respectively equal to 0.64 \AA and 0.74 \AA . Only a substitution of Bi by Ag should be possible in this secondary phase, which formula should be then close to $(\text{Bi}_{0.75-x}\text{Ag}_x\text{Zn}_{0.25})_2(\text{Nb}_{0.75}\text{Zn}_{0.25})_2\text{O}_{7-2x}$. Oxygen defect can lead to a smaller cell parameter of the structure which could explain a shift of the peaks numbered “1” toward high angle of the diffractogram in regard of the reference datasheet (JPDF File no. 54-0971).

The electrical and dielectric measurements of these samples show a high dielectric constant ($\epsilon_r=25.5$), a resistivity above $10^{12} \Omega \text{ cm}$, but important losses ($\tan(\delta)\approx 0.5\%$). As bismuth based pyrochlores, without Ag, have good dielectric properties [13,14], these losses could be correlated to Bi substitutions by Ag in this secondary phase which lead to vacancies on the anionic network and could induce an ionic conduction.

ZnNb_2O_6 with BSBa additive pellets sintered without Ag had a secondary phase, not detectable by XRD but only observed with SEM, rich in Ba and Si elements. When co-sintered with an Ag electrode, XRD measurements show two new secondary phases (Fig. 10): Zn_2SiO_4 and a phase isomorphic to $\text{Ba}_2\text{NaNb}_5\text{O}_{15}$ (00-040-1463) which has a tetragonal bronze tungsten crystalline structure.

SEM BSE/EDX microstructural analyses do not show any presence of pure Ag in bulk but clearly indicate that three different phases co-exist (Fig. 11). The composition of the dark grey areas is close to the one of Zn_2SiO_4 , while the light ones are characterised by the following elements ratio: Nb:49 at%, Ag:12 at% and Ba:18 at%. As for Ag co-sintered pellets made with $\text{ZnNb}_2\text{O}_6+5 \text{ wt\% BZBi}$, left part of Fig. 11 (Ag electrode on top) shows that this new phase has an inhomogeneous size along the sample's thickness ($\approx 1 \text{ mm}$). In this bright phase, Ag concentration is nearly constant in all the sample thickness and it seems that Ag diffusion still took place through a medium of pores and concentrates in this new secondary phase. This phase migrates easily in the material too, so we can also

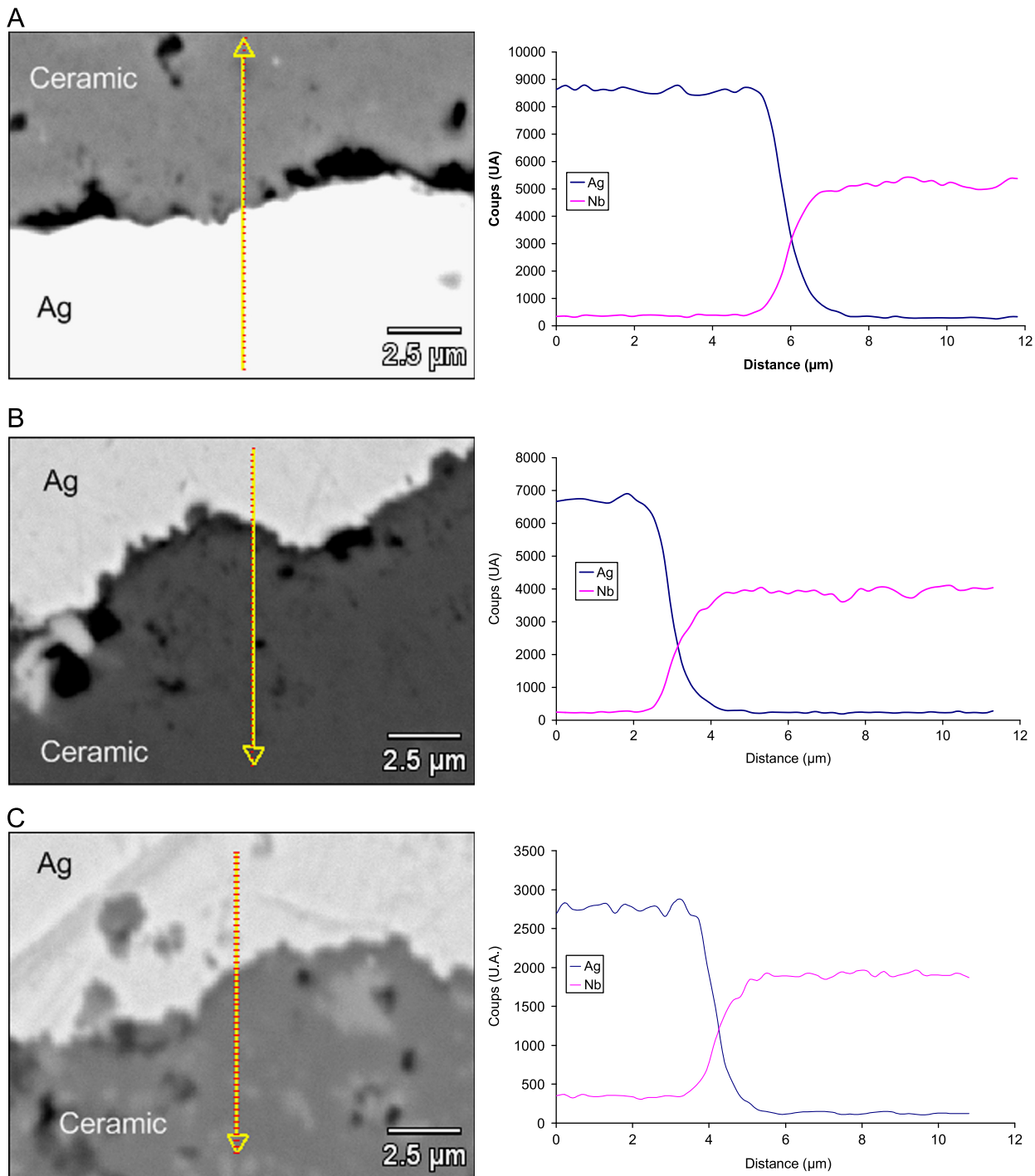


Fig. 6. Ag co-sintered samples profiles. (a) ZnNb₂O₆+5 wt% BZs, (b) ZnNb₂O₆+5 wt% BZBi and (c) ZnNb₂O₆+5 wt% BSBa.

consider that it is involved in the sintering mechanisms. Considering diffractogram and atomic quantification in the bright areas, this secondary phase should be Ba₂AgNb₅O₁₅. Medium grey area is ZnNb₂O₆ with a zinc deficit (Zn: 31 at% and Nb: 69 at%). Missing Zn should have migrated to form the dark grey secondary phase Zn₂SiO₄.

When compared to samples sintered without Ag, these samples have a lower permittivity ($\epsilon_r=20.3$), lower losses ($\tan(\delta)<0.1\%$) and a higher resistivity ($\rho>10^{12}\ \Omega\ \text{cm}$).

Ag co-sintering seems to improve some characteristics of this material, but Ag detected in bright areas could be detrimental to breakdown electric field [15] and to life span [16] of components made with this composition.

Permittivity and dielectrical losses measurements vs. temperature have been done for Ag co-sintered pellets (Fig. 12).

ZnNb₂O₆+5 wt% BZBi material has its permittivity and losses values increasing with the temperature showing the existence of semi-conduction. This result is in good agreement

with the assumption previously made about a possible ionic conduction due to anionic vacancies because of the substitution of Bi by Ag in the pyrochlore secondary phase.

Contrariwise, when compared to non-co-sintered samples, it can be observed that Ag co-sintered ZnNb_2O_6 with BZS or BSBa glass

frit additions have the same behaviour when measured from $-32\text{ }^\circ\text{C}$ to $+145\text{ }^\circ\text{C}$: they are still class I dielectric materials.

4. Conclusions

Commercial glass frits additives based on $\text{B}_2\text{O}_3\text{--ZnO--SiO}_2$, $\text{B}_2\text{O}_3\text{--ZnO--Bi}_2\text{O}_3$ and $\text{B}_2\text{O}_3\text{--SiO}_2\text{--BaO}$ can sufficiently lower the sintering temperature of ZnNb_2O_6 to make it compatible with Ag electrodes for LTCC applications. Moreover, in the case of BZS additions, we have shown with comparison to the literature the ability to lower the sintering temperature to $900\text{ }^\circ\text{C}$ together with the obtaining of improved microwave properties ($QF=23,070\text{ GHz}$ at $900\text{ }^\circ\text{C}$ instead of $QF=12,800\text{ GHz}$ at $925\text{ }^\circ\text{C}$ [8]).

The material based on BZBi glass frit owns as well good electric and dielectric characteristics. But, when co-sintered with Ag, the presence of a secondary phase (containing Ag) induced in this case high dielectric losses.

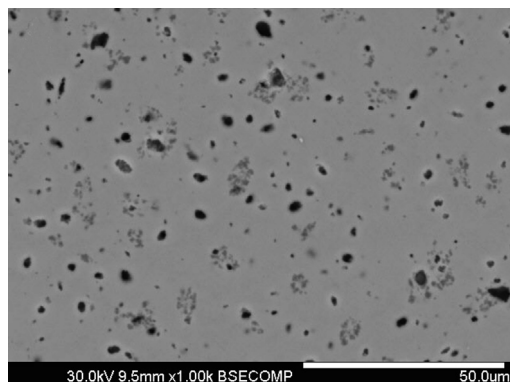


Fig. 7. Microstructure of ZnNb_2O_6 +5 wt% BZS Ag co-sintered at $900\text{ }^\circ\text{C}$ for 4 h.

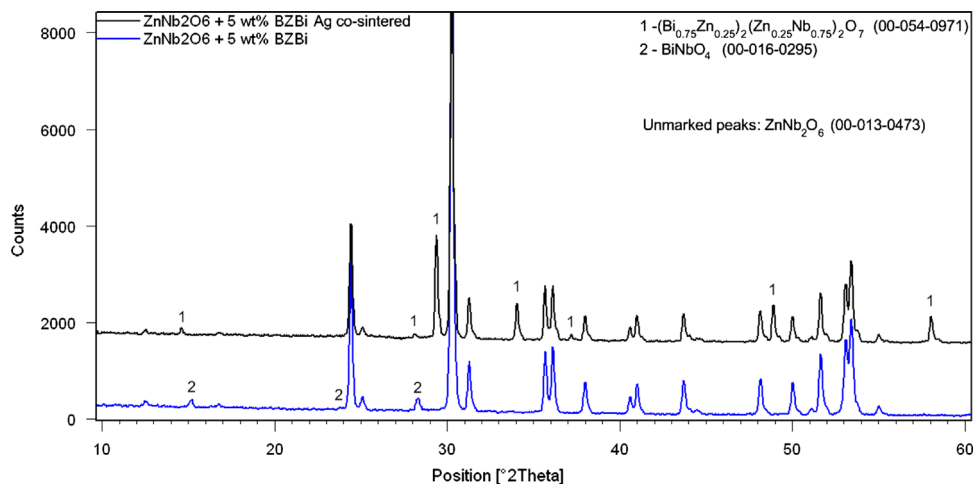


Fig. 8. ZnNb_2O_6 +5 wt% BZBi diffractograms of ceramics sintered alone or co-sintered with Ag at $900\text{ }^\circ\text{C}$ for 4 h.

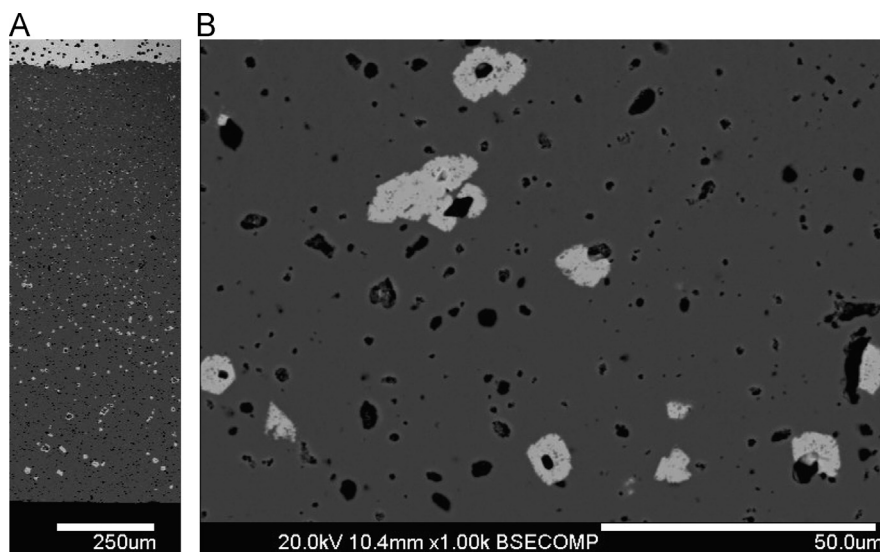


Fig. 9. Evolution of microstructure of ZnNb_2O_6 +5 wt% BZBi Ag co-sintered at $900\text{ }^\circ\text{C}$ for 4 h, between Ag electrode and surface of sample (A: general view and B: detail).

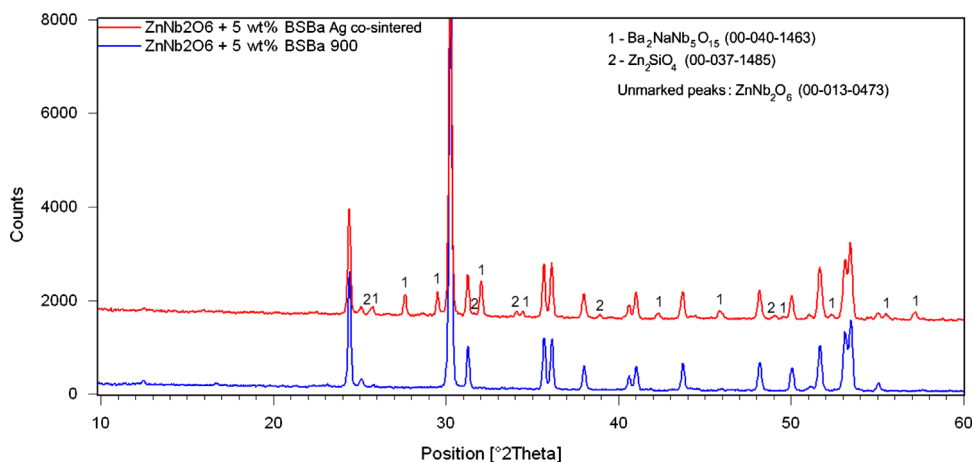


Fig. 10. ZnNb₂O₆+5 wt% BSBA diffractograms of ceramics sintered alone or co-sintered with Ag at 900 °C for 8 h.

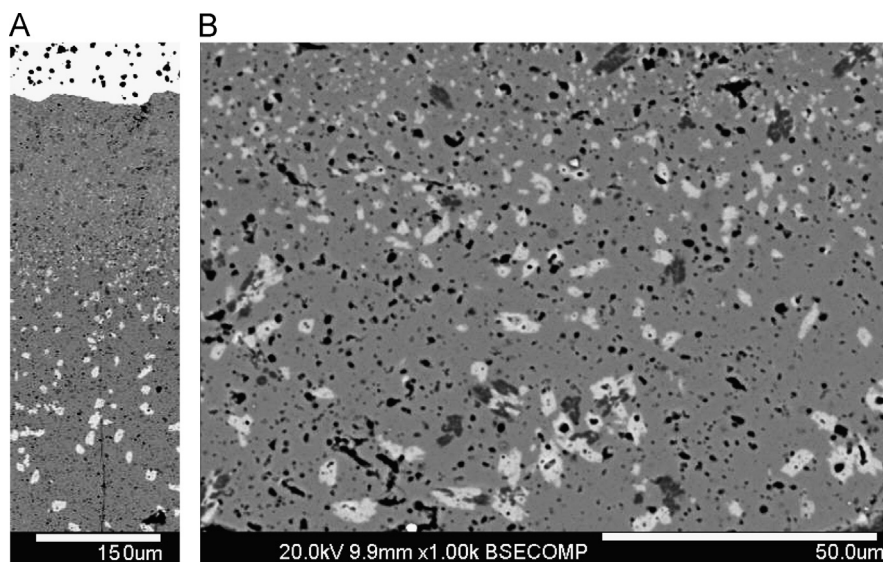


Fig. 11. Evolution of microstructure of ZnNb₂O₆+5 wt% BSBA Ag co-sintered at 900 °C for 8 h, between Ag electrode and surface of sample (A: general view and B: detail).

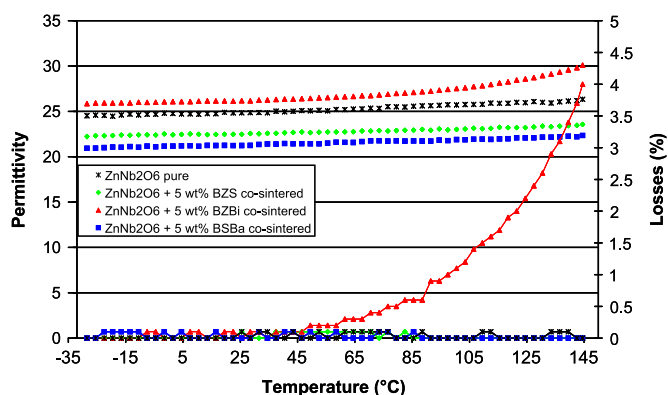


Fig. 12. Dielectric properties vs. temperature of pellets co-sintered with Ag.

For BSBA glass frit addition we also observe type I properties even when Ag co-sintered samples have good properties, nonetheless Ag presence in one of the two secondary phases.

From the three studied compositions, ZnNb₂O₆+5 wt% BZS is the one with the best electric and dielectric properties: $\epsilon_r=21.1$, $\tan(\delta) < 0.1$, $\rho > 10^{12} \Omega \text{ cm}$, $\tau_e = +147 \text{ ppm } ^\circ\text{C}^{-1}$, $QF=23,070 \text{ GHz}$ when sintered at 900 °C for 1 h alone or co-sintered with Ag. With this material type I MLCC with Ag inner electrodes can be considered. We are now studying the aging behaviour under electric field and proceeding climatic studies of multilayer capacitors prototypes.

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